



Welcome to E-XFL.COM

Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	295
Number of Logic Elements/Cells	-
Total RAM Bits	-
Number of I/O	57
Number of Gates	1200
Voltage - Supply	4.5V ~ 5.5V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	68-LCC (J-Lead)
Supplier Device Package	68-PLCC (24.23x24.23)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/a1010b-1pl68c

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



The systems are available for 386/486/PentiumTM PC and for HPTM and SunTM workstations and for running Viewlogic[®],

Mentor Graphics[®], CadenceTM, OrCADTM, and Synopsys design environments.

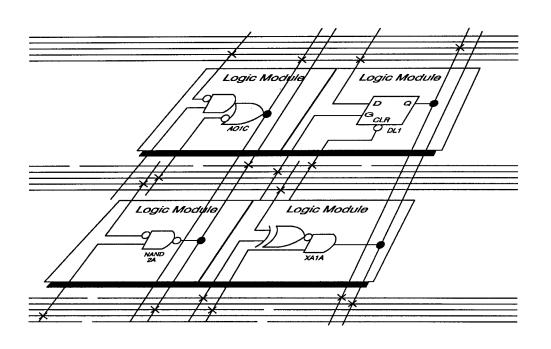


Figure 1 • Partial View of an ACT 1 Device

ACT 1 Device Structure

A partial view of an ACT 1 device (Figure 1) depicts four logic modules and distributed horizontal and vertical interconnect tracks. PLICE antifuses, located at intersections of the horizontal and vertical tracks, connect logic module inputs and outputs. During programming, these antifuses are addressed and programmed to make the connections required by the circuit application.

The ACT 1 Logic Module

The ACT 1 logic module is an 8-input, one-output logic circuit chosen for the wide range of functions it implements and for its efficient use of interconnect routing resources (Figure 2).

The logic module can implement the four basic logic functions (NAND, AND, OR, and NOR) in gates of two, three, or four inputs. Each function may have many versions, with different combinations of active-low inputs. The logic module can also implement a variety of D-latches, exclusivity functions, AND-ORs, and OR-ANDs. No dedicated hardwired latches or flip-flops are required in the array, since latches and flip-flops may be constructed from logic modules wherever needed in the application.

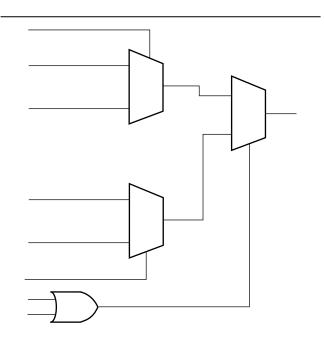


Figure 2 • ACT 1 Logic Module

I/O Buffers

Each I/O pin is available as an input, output, three-state, or bidirectional buffer. Input and output levels are compatible with standard TTL and CMOS specifications. Outputs sink or

source 10 mA at TTL levels. See Electrical Specifications for additional I/O buffer specifications.

Device Organization

ACT 1 devices consist of a matrix of logic modules arranged in rows separated by wiring channels. This array is surrounded by a ring of peripheral circuits including I/O buffers, testability circuits, and diagnostic probe circuits providing real-time diagnostic capability. Between rows of logic modules are routing channels containing sets of segmented metal tracks with PLICE antifuses. Each channel has 22 signal tracks. Vertical routing is permitted via 13 vertical tracks per logic module column. The resulting network allows arbitrary and flexible interconnections between logic modules and I/O modules.

Probe Pin

ACT 1 devices have two independent diagnostic probe pins. These pins allow the user to observe any two internal signals by entering the appropriate net name in the diagnostic software. Signals may be viewed on a logic analyzer using Actel's Actionprobe[®] diagnostic tools. The probe pins can also be used as user-defined I/Os when debugging is finished.

Ordering Information

ACT 1 Array Performance

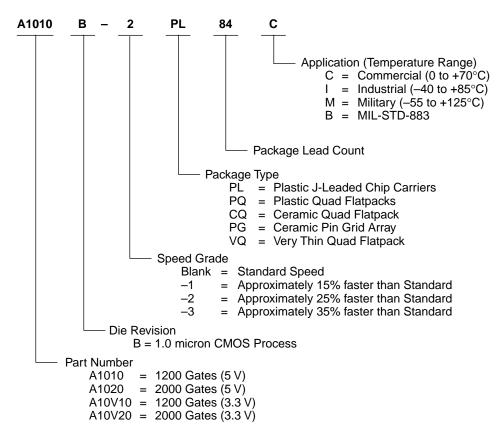
Temperature and Voltage Effects

Worst-case delays for ACT 1 arrays are calculated in the same manner as for masked array products. A typical delay parameter is multiplied by a derating factor to account for temperature, voltage, and processing effects. However, in an ACT 1 array, temperature and voltage effects are less dramatic than with masked devices. The electrical characteristics of module interconnections on ACT 1 devices remain constant over voltage and temperature fluctuations.

As a result, the total derating factor from typical to worst-case for a standard speed ACT 1 array is only 1.19 to 1, compared to 2 to 1 for a masked gate array.

Logic Module Size

Logic module size also affects performance. A mask programmed gate array cell with four transistors usually implements only one logic level. In the more complex logic module (similar to the complexity of a gate array macro) of an ACT 1 array, implementation of multiple logic levels within a single module is possible. This eliminates interlevel wiring and associated RC delays. The effect is termed "net compression."





Product Plan

		Speed	Grade*			Α	pplicati	on
	Std	-1	-2	-3	С	I	М	В
A1010B Device								
44-pin Plastic Leaded Chip Carrier (PL)	~	~	~	~	~	~	_	
68-pin Plastic Leaded Chip Carrier (PL)	~	~	~	~	~	~	_	_
100-pin Plastic Quad Flatpack (PQ)	~	~	~	~	~	~	—	—
80-pin Very Thin (1.0 mm) Quad Flatpack (VQ)	~	~	~	~	~		_	_
84-pin Ceramic Pin Grid Array (PG)	~	~	—	—	~	—	~	~
A1020B Device								
44-pin Plastic Leaded Chip Carrier (PL)	~	~	~	~	~	~	_	_
68-pin Plastic Leaded Chip Carrier (PL)	~	~	~	~	~	~	_	_
84-pin Plastic Leaded Chip Carrier (PL)	~	~	~	~	~	~	—	_
100-pin Plastic Quad Flatpack (PQ)	~	~	~	~	~	~	—	—
80-pin Very Thin (1.0 mm) Quad Flatpack (VQ)	~	~	~	~	~		_	_
84-pin Ceramic Pin Grid Array (PG)	~	~	_	_	~		~	~
84-pin Ceramic Quad Flatpack (CQ)	~	~	—	—	~	—	~	~
A10V10B Device								
68-pin Plastic Leaded Chip Carrier (PL)	~	_	_	_	~	_	_	_
80-pin Very Thin (1.0 mm) Quad Flatpack (VQ)	~	_	_	—	~	_	_	_
A10V20B Device								
68-pin Plastic Leaded Chip Carrier (PL)	~	_		_	~	_	_	_
84-pin Plastic Leaded Chip Carrier (PL)	~	—	—	—	~		_	_
80-pin Very Thin (1.0 mm) Quad Flatpack (VQ)	~	_			~	_		
Applications: C = Commercial Availability: ✓ I = Industrial P M = Military — B = MIL-STD-883	= Plann		* Speed		Approx. 15 Approx. 25 Approx. 35	5% faste	r than S	tandard

Device Resources

					User I/Os		
Device	Logic Modules	Gates	44-pin	68-pin	80-pin	84-pin	100-pin
A1010B, A10V10B	295	1200	34	57	57	57	57
A1020B, A10V20B	547	2000	34	57	69	69	69

Pin Description

CLK Clock (Input)

TTL Clock input for global clock distribution network. The Clock input is buffered prior to clocking the logic modules. This pin can also be used as an I/O.

DCLK Diagnostic Clock (Input)

TTL Clock input for diagnostic probe and device programming. DCLK is active when the MODE pin is HIGH. This pin functions as an I/O when the MODE pin is LOW.

GND Ground

Input LOW supply voltage.

I/O Input/Output (Input, Output)

I/O pin functions as an input, output, three-state, or bidirectional buffer. Input and output levels are compatible with standard TTL and CMOS specifications. Unused I/O pins are automatically driven LOW by the ALS software.

MODE Mode (Input)

The MODE pin controls the use of multifunction pins (DCLK, PRA, PRB, SDI). When the MODE pin is HIGH, the special functions are active. When the MODE pin is LOW, the pins function as I/O. To provide Actionprobe capability, the MODE pin should be terminated to GND through a 10K resistor so that the MODE pin can be pulled high when required.

NC No Connection

This pin is not connected to circuitry within the device.

PRA Probe A (Output)

The Probe A pin is used to output data from any user-defined design node within the device. This independent diagnostic pin is used in conjunction with the Probe B pin to allow real-time diagnostic output of any signal path within the device. The Probe A pin can be used as a user-defined I/O when debugging has been completed. The pin's probe capabilities can be permanently disabled to protect the programmed design's confidentiality. PRA is active when the MODE pin is HIGH. This pin functions as an I/O when the MODE pin is LOW.

PRB Probe B (Output)

The Probe B pin is used to output data from any user-defined design node within the device. This independent diagnostic pin is used in conjunction with the Probe A pin to allow real-time diagnostic output of any signal path within the device. The Probe B pin can be used as a user-defined I/O when debugging has been completed. The pin's probe capabilities can be permanently disabled to protect the programmed design's confidentiality. PRB is active when the MODE pin is HIGH. This pin functions as an I/O when the MODE pin is LOW.

SDI Serial Data Input (Input)

Serial data input for diagnostic probe and device programming. SDI is active when the MODE pin is HIGH. This pin functions as an I/O when the MODE pin is LOW.

V_{CC} Supply Voltage Input HIGH supply voltage.

Absolute Maximum Ratings¹

Free air temperature range

Symbol	Parameter	Limits	Units
V _{CC}	DC Supply Voltage ²	-0.5 to +7.0	Volts
VI	Input Voltage	–0.5 to V _{CC} +0.5	Volts
V _O	Output Voltage	–0.5 to V _{CC} +0.5	Volts
I _{IO}	I/O Sink/Source Current ³	±20	mA
T _{STG}	Storage Temperature	-65 to +150	°C
17 /			

Notes:

1. Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. Exposure to absolute maximum rated conditions for extended periods may affect device reliability. Device should not be operated outside the Recommended Operating Conditions.

- 2. $V_{PP} = V_{CC}$, except during device programming.
- 3. Device inputs are normally high impedance and draw extremely low current. However, when input voltage is greater than V_{CC} + 0.5 V or less than GND 0.5 V, the internal protection diode will be forward biased and can draw excessive current.

Recommended Operating Conditions

Parameter	Commercial	Industrial	Military	Units
Temperature Range ¹	0 to +70	–40 to +85	–55 to +125	°C
Power Supply Tolerance	±5	±10	±10	%V _{CC}

Note:

1. Ambient temperature (T_A) used for commercial and industrial; case temperature (T_C) used for military.



Electrical Specifications (5V)

		Com	mercial	Ind	ustrial	Mi	litary	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Units
	$(I_{OH} = -10 \text{ mA})^2$	2.4						V
V _{OH} ¹	(I _{OH} = -6 mA)	3.84						V
	(I _{OH} = -4 mA)			3.7		3.7		V
v 1	(I _{OL} = 10 mA) ²		0.5					V
V _{OL} ¹	(I _{OL} = 6 mA)		0.33		0.40		0.40	V
V _{IL}		-0.3	0.8	-0.3	0.8	-0.3	0.8	V
V _{IH}		2.0	V _{CC} + 0.3	2.0	V _{CC} + 0.3	2.0	V _{CC} + 0.3	V
Input Transition Ti	ime t _R , t _F ²		500		500		500	ns
C _{IO} I/O Capacitar	nce ^{2, 3}		10		10		10	pF
Standby Current,	I_{CC}^{4} (typical = 1 mA)		3		10		20	mA
Leakage Current ⁵	5	-10	10	-10	10	-10	10	μA

Notes:

1. Only one output tested at a time. $V_{CC} = min$.

2. Not tested, for information only.

3. Includes worst-case 84-pin PLCC package capacitance. V_{OUT} = 0 V, f = 1 MHz.

4. Typical standby current = 1 mA. All outputs unloaded. All inputs = V_{CC} or GND.

5. $V_0, V_{IN} = V_{CC} \text{ or } GND.$

Electrical Specifications (3.3V)

Parameter		Com	Commercial			
		Min.	Max.	Units		
y. 1	(I _{OH} = -4 mA)	2.15		V		
V _{OH} ¹	(I _{OH} = -3.2 mA)	2.4		V		
V _{OL} ¹	(I _{OL} = 6 mA)		0.4	V		
V _{IL}		-0.3	0.8	V		
V _{IH}		2.0	V _{CC} + 0.3	V		
Input Transition Time t _F	$_{R}, t_{F}^{2}$		500	ns		
C _{IO} I/O Capacitance ^{2, 3}	3		10	pF		
Standby Current, I_{CC}^4	(typical = 0.3 mA)		0.75	mA		
Leakage Current ⁵		-10	10	μΑ		

Notes:

1. Only one output tested at a time. $V_{CC} = min$.

2. Not tested, for information only.

3. Includes worst-case 84-pin PLCC package capacitance. V_{OUT} = 0 V, f = 1 MHz.

4. Typical standby current = 0.3 mA. All outputs unloaded. All inputs = V_{CC} or GND.

5. V_{O} , $V_{IN} = V_{CC}$ or GND

Package Thermal Characteristics

The device junction to case thermal characteristics is θ jc, and the junction to ambient air characteristics is θ ja. The thermal characteristics for θ ja are shown with two different air flow rates. Maximum junction temperature is 150°C.

A sample calculation of the maximum power dissipation for an 84-pin plastic leaded chip carrier at commercial temperature is as follows:

$$\frac{\text{Max junction temp.(°C)} - \text{Max commercial temp.(°C)}}{\theta ja(°C/W)} = \frac{150°C - 70°C}{37°C/W} = 2.2 \text{ W}$$

Package Type	Pin Count	θ jc	θja Still Air	θja 300 ft/min	Units
	44	15	45	35	°C/W
Plastic J-Leaded Chip Carrier	68	13	38	29	°C/W
	84	12	37	28	°C/W
Plastic Quad Flatpack	100	13	48	40	°C/W
Very Thin (1.0 mm) Quad Flatpack	80	12	43	35	°C/W
Ceramic Pin Grid Array	84	8	33	20	°C/W
Ceramic Quad Flatpack	84	5	40	30	°C/W

General Power Equation

$$\begin{split} P &= \left[I_{CC} standby + I_{CC} active\right] * V_{CC} + I_{OL} * V_{OL} * N + I_{OH} * \\ \left(V_{CC} - V_{OH}\right) * M \end{split}$$

Where:

 I_{CC} standby is the current flowing when no inputs or outputs are changing.

I_{CC}active is the current flowing due to CMOS switching.

I_{OL}, I_{OH} are TTL sink/source currents.

V_{OL}, V_{OH} are TTL level output voltages.

N equals the number of outputs driving TTL loads to $V_{\mbox{\scriptsize OL}}$

M equals the number of outputs driving TTL loads to $V_{\mbox{\scriptsize OH}}.$

An accurate determination of N and M is problematical because their values depend on the family type, design details, and on the system I/O. The power can be divided into two components: static and active.

Static Power Component

Actel FPGAs have small static power components that result in lower power dissipation than PALs or PLDs. By integrating multiple PALs/PLDs into one FPGA, an even greater reduction in board-level power dissipation can be achieved. The power due to standby current is typically a small component of the overall power. Standby power is calculated below for commercial, worst case conditions.

I _{CC}	V _{CC}	Power
3 mA	5.25 V	15.75 mW (max)
1 mA	5.25 V	5.25 mW (typ)
0.75 mA	3.60 V	2.70 mW (max)
0.30 mA	3.30 V	0.99 mW (typ)

Active Power Component

Power dissipation in CMOS devices is usually dominated by the active (dynamic) power dissipation. This component is frequency dependent, a function of the logic and the

external I/O. Active power dissipation results from charging internal chip capacitances of the interconnect, unprogrammed antifuses, module inputs, and module outputs, plus external capacitance due to PC board traces and load device inputs. An additional component of the active power dissipation is the totem-pole current in CMOS transistor pairs. The net effect can be associated with an equivalent capacitance that can be combined with frequency and voltage to represent active power dissipation.



Equivalent Capacitance

The power dissipated by a CMOS circuit can be expressed by the Equation 1.

Power (uW) =
$$C_{EQ} * V_{CC2} * F$$
 (1)

Where:

C_{EQ} is the equivalent capacitance expressed in pF.

V_{CC} is the power supply in volts.

F is the switching frequency in MHz.

Equivalent capacitance is calculated by measuring I_{CC} active at a specified frequency and voltage for each circuit component of interest. Measurements have been made over a range of frequencies at a fixed value of V_{CC} . Equivalent capacitance is frequency independent so that the results may be used over a wide range of operating conditions. Equivalent capacitance values are shown below.

CEQ Values for Actel FPGAs

	A10V10B A10V20B	A1010B A1020B
Modules (C _{EQM})	3.2	3.7
Input Buffers (_{CEQI})	10.9	22.1
Output Buffers (C _{EQO})	11.6	31.2
Routed Array Clock Buffer		
Loads (C _{EQCR})	4.1	4.6

To calculate the active power dissipated from the complete design, the switching frequency of each part of the logic must be known. Equation 2 shows a piece-wise linear summation over all components.

$$Power = V_{CC}^{2*} [(m * C_{EQM} * f_m)_{modules} + (n * C_{EQI} * f_n)_{inputs} + (p * (C_{EQ0} + C_L) * f_p)_{outputs} + 0.5* (q_1 * C_{EQCR} * f_{q1})_{routed_Clk1} + (r_1 * f_{q1})_{routed_Clk1}]$$
(2)

Where:

- m = Number of logic modules switching at fm
- n = Number of input buffers switching at fn
- p = Number of output buffers switching at fp
- q₁ = Number of clock loads on the first routed array clock (All families)
- r₁ = Fixed capacitance due to first routed array clock (All families)

- C_{EQM} = Equivalent capacitance of logic modules in pF
- C_{EQI} = Equivalent capacitance of input buffers in pF
- C_{EQ0} = Equivalent capacitance of output buffers in pF
- - = Output lead capacitance in pF

C_L

fm

fn

fp

f_{q1}

- = Average logic module switching rate in MHz
- = Average input buffer switching rate in MHz
- = Average output buffer switching rate in MHz
- Average first routed array clock rate in MHz (All families)

Fixed Capacitance Values for Actel FPGAs (pF)

Device Type	r ₁ routed_Clk1
A1010B	41.4
A1020B	68.6
A10V10B	40
A10V20B	65

Determining Average Switching Frequency

To determine the switching frequency for a design, you must have a detailed understanding of the data input values to the circuit. The following guidelines are meant to represent worst-case scenarios so that they can be generally used to predict the upper limits of power dissipation. These guidelines are as follows:

Logic Modules (m)	90% of modules
Inputs switching (n)	#inputs/4
Outputs switching (p)	#outputs/4
First routed array clock loads (q_1)	40% of modules
Load capacitance (C_L)	35 pF
Average logic module switching rate (f_m)	F/10
Average input switching rate (f_n)	F/5
Average output switching rate (f _p)	F/10
Average first routed array clock rate (f_{q1})	F

Functional Timing Tests

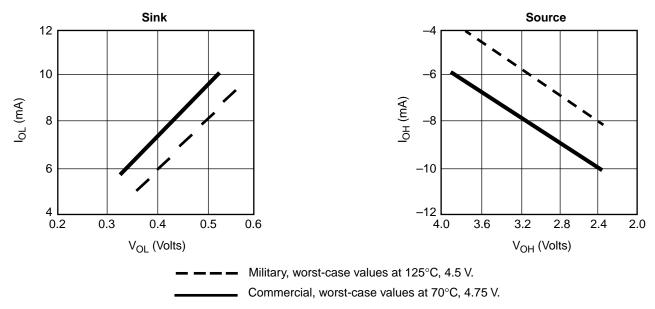
AC timing for logic module internal delays is determined after place and route. The DirectTime Analyzer utility displays actual timing parameters for circuit delays. ACT 1 devices are AC tested to a "binning" circuit specification.

The circuit consists of one input buffer + n logic modules + one output buffer (n = 16 for A1010B; n = 28 for A1020B). The

Output Buffer Performance Derating (5V)

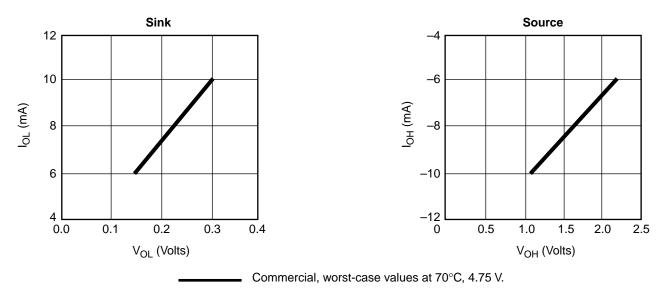
logic modules are distributed along two sides of the device, as inverting or non-inverting buffers. The modules are connected through programmed antifuses with typical capacitive loading.

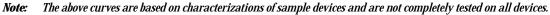
Propagation delay $[t_{PD} = (t_{PLH} + t_{PHL})/2]$ is tested to the following AC test specifications.



Note: The above curves are based on characterizations of sample devices and are not completely tested on all devices.







Timing Derating

A best case timing derating factor of 0.45 is used to reflect best case processing. Note that this factor is relative to the "standard speed" timing parameters, and must be multiplied by the appropriate voltage and temperature derating factors for a given application.

Timing Derating Factor (Temperature and Voltage)

	Industrial		Mili	tary
	Min.	Max.	Min.	Max.
(Commercial Minimum/Maximum Specification) x	0.69	1.11	0.67	1.23

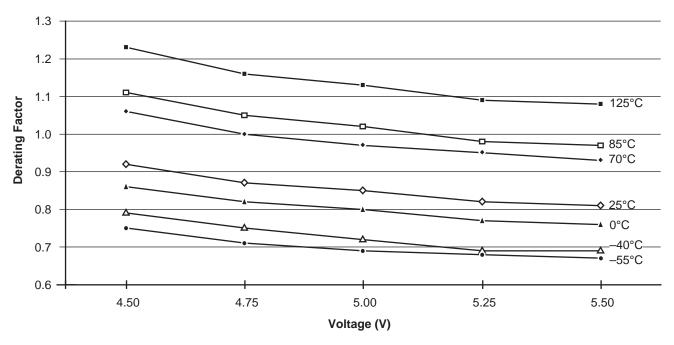
Timing Derating Factor for Designs at Typical Temperature ($T_J = 25^{\circ}C$) and Voltage (5.0 V)

(Commercial Maximum Specification) x	0.85
--------------------------------------	------

Temperature and Voltage Derating Factors (normalized to Worst-Case Commercial, $T_J = 4.75 V$, 70°C)

	-55	-40	0	25	70	85	125
4.50	0.75	0.79	0.86	0.92	1.06	1.11	1.23
4.75	0.71	0.75	0.82	0.87	1.00	1.05	1.16
5.00	0.69	0.72	0.80	0.85	0.97	1.02	1.13
5.25	0.68	0.69	0.77	0.82	0.95	0.98	1.09
5.50	0.67	0.69	0.76	0.81	0.93	0.97	1.08

Junction Temperature and Voltage Derating Curves (normalized to Worst-Case Commercial, $T_J = 4.75 \text{ V}, 70^{\circ}\text{C}$)



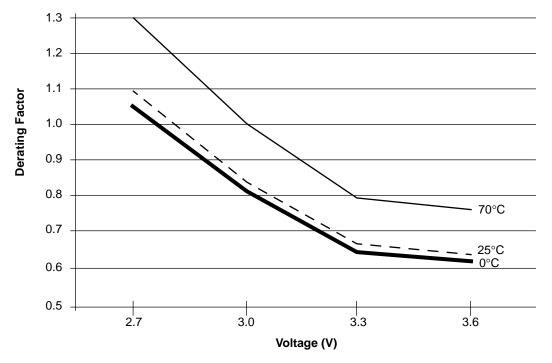
Note: This derating factor applies to all routing and propagation delays.



Temperature and Voltage Derating Factors (normalized to Worst-Case Commercial, $T_J = 3.0 V$, $70^{\circ}C$)

	0	25	70
2.7	1.05	1.09	1.30
3.0	0.81	0.84	1.00
3.3	0.64	0.67	0.79
3.6	0.62	0.64	0.76

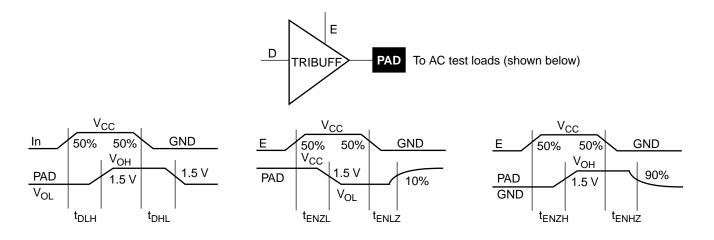
Junction Temperature and Voltage Derating Curves (normalized to Worst-Case Commercial, $T_J = 3.0 \text{ V}, 70^{\circ}\text{C}$)



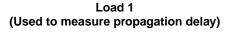
Note: This derating factor applies to all routing and propagation delays.

Parameter Measurement

Output Buffer Delays

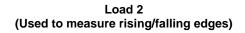


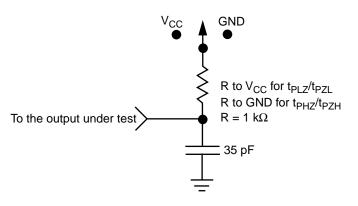
AC Test Loads

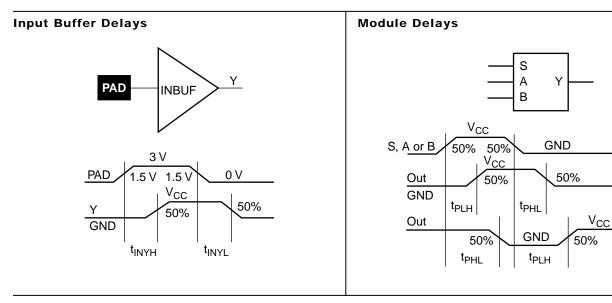


35 pF

To the output under test







ACT 1 Timing Characteristics

Logic Modu	le Propagation Delays	'-3' Speed		'-2' Speed		'–1' S	Speed	'Std'	Speed	3.3 V Speed		
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Units
t _{PD1}	Single Module		2.9		3.4		3.8		4.5		6.5	ns
t _{PD2}	Dual Module Macros		6.8		7.8		8.8		10.4		15.1	ns
t _{CO}	Sequential Clk to Q		2.9		3.4		3.8		4.5		6.5	ns
t _{GO}	Latch G to Q		2.9		3.4		3.8		4.5		6.5	ns
t _{RS}	Flip-Flop (Latch) Reset to Q		2.9		3.4		3.8		4.5		6.5	ns
Predicted R	outing Delays ²											
t _{RD1}	FO=1 Routing Delay		0.9		1.1		1.2		1.4		2.0	ns
t _{RD2}	FO=2 Routing Delay		1.4		1.7		1.9		2.2		3.2	ns
t _{RD3}	FO=3 Routing Delay		2.1		2.5		2.8		3.3		4.8	ns
t _{RD4}	FO=4 Routing Delay		3.1		3.6		4.1		4.8		7.0	ns
t _{RD8}	FO=8 Routing Delay		6.6		7.7		8.7		10.2		14.8	ns
Sequential 7	Timing Characteristics ³											
t _{SUD}	Flip-Flop (Latch) Data Input Setup	5.5		6.4		7.2		8.5		10.0		ns
t _{HD} ⁴	Flip-Flop (Latch) Data Input Hold	0.0		0.0		0.0		0.0		0.0		ns
t _{SUENA}	Flip-Flop (Latch) Enable Setup	5.5		6.4		7.2		8.5		10.0		ns
t _{HENA}	Flip-Flop (Latch) Enable Hold	0.0		0.0		0.0		0.0		0.0		ns
t _{WCLKA}	Flip-Flop (Latch) Clock Active Pulse Width	6.8		8.0		9.0		10.5		9.8		ns
t _{WASYN}	Flip-Flop (Latch) Asynchronous Pulse Width	6.8		8.0		9.0		10.5		9.8		ns
t _A	Flip-Flop Clock Input Period	14.2		16.7		18.9		22.3		20.0		ns
f _{MAX}	Flip-Flop (Latch) Clock Frequency (FO = 128)		70		60		53		45		50	MHz

(Worst-Case Commercial Conditions, $V_{CC} = 4.75 \text{ V}$, $T_J = 70^{\circ}\text{C})^1$

Notes:

1. $V_{CC} = 3.0 V$ for 3.3V specifications.

2. Routing delays are for typical designs across worst-case operating conditions. These parameters should be used for estimating device performance. Post-route timing analysis or simulation is required to determine actual worst-case performance. Post-route timing is based on actual routing delay measurements performed on the device prior to shipment.

3. Setup times assume fanout of 3. Further testing information can be obtained from the DirectTime Analyzer utility.

4. The Hold Time for the DFME1A macro may be greater than 0 ns. Use the Designer 3.0 or later Timer to check the Hold Time for this macro.



ACT 1 Timing Characteristics (continued)

(Worst-Case Commercial Conditions)

Input Modu	ule Propagation Delays		'–3' S	Speed	'–2' S	Speed	'–1' S	Speed	'Std' S	Speed	3.3 V	Speed	
Parameter	Description		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Units
t _{INYH}	Pad to Y High			3.1		3.5		4.0		4.7		6.8	ns
t _{INYL}	Pad to Y Low			3.1		3.5		4.0		4.7		6.8	ns
Input Modu	ule Predicted Routing D	elays ¹											
t _{IRD1}	FO=1 Routing Delay			0.9		1.1		1.2		1.4		2.0	ns
t _{IRD2}	FO=2 Routing Delay			1.4		1.7		1.9		2.2		3.2	ns
t _{IRD3}	FO=3 Routing Delay			2.1		2.5		2.8		3.3		4.8	ns
t _{IRD4}	FO=4 Routing Delay			3.1		3.6		4.1		4.8		7.0	ns
t _{IRD8}	FO=8 Routing Delay			6.6		7.7		8.7		10.2		14.8	ns
Global Clo	ck Network												
^t скн	Input Low to High	FO = 16 FO = 128		4.9 5.6		5.6 6.4		6.4 7.3		7.5 8.6		6.7 7.9	ns
t _{CKL}	Input High to Low	FO = 16 FO = 128		6.4 7.0		7.4 8.1		8.4 9.2		9.9 10.8		8.8 10.0	ns
t _{PWH}	Minimum Pulse Width High	FO = 16 FO = 128	6.5 6.8		7.5 8.0		8.5 9.0		10.0 10.5		8.9 9.8		ns
t _{PWL}	Minimum Pulse Width Low	FO = 16 FO = 128	6.5 6.8		7.5 8.0		8.5 9.0		10.0 10.5		8.9 9.8		ns
t _{CKSW}	Maximum Skew	FO = 16 FO = 128		1.2 1.8		1.3 2.1		1.5 2.4		1.8 2.8		1.5 2.4	ns
t _P	Minimum Period	FO = 16 FO = 128	13.2 14.2		15.4 16.7		17.6 18.9		20.9 22.3		18.2 20		ns
f _{MAX}	Maximum Frequency	FO = 16 FO = 128		75 70		65 60		57 53		48 45		55 50	MHz

Note:

1. These parameters should be used for estimating device performance. Optimization techniques may further reduce delays by 0 to 4 ns. Routing delays are for typical designs across worst-case operating conditions. Post-route timing analysis or simulation is required to determine actual worst-case performance. Post-route timing is based on actual routing delay measurements performed on the device prior to shipment.

ACT 1 Timing Characteristics (continued)

Output Mo	dule Timing	'–3' Speed	'-2' Speed	'-1' Speed	'Std' Speed	3.3 V Speed	
Parameter	Description	Min. Max.	Min. Max.	Min. Max.	Min. Max.	Min. Max.	Units
TTL Outpu	t Module Timing ¹						
t _{DLH}	Data to Pad High	6.7	7.6	8.7	10.3	15.0	ns
t _{DHL}	Data to Pad Low	7.5	8.6	9.8	11.5	16.7	ns
t _{ENZH}	Enable Pad Z to High	6.6	7.5	8.6	10.2	14.8	ns
t _{ENZL}	Enable Pad Z to Low	7.9	9.1	10.4	12.2	17.7	ns
t _{ENHZ}	Enable Pad High to Z	10.0	11.6	13.1	15.4	22.4	ns
t _{ENLZ}	Enable Pad Low to Z	9.0	10.4	11.8	13.9	20.2	ns
d _{TLH}	Delta Low to High	0.06	0.07	0.08	0.09	0.13	ns/pF
d _{THL}	Delta High to Low	0.08	0.09	0.10	0.12	0.17	ns/pF
CMOS Out	put Module Timing ¹						
t _{DLH}	Data to Pad High	7.9	9.2	10.4	12.2	17.7	ns
t _{DHL}	Data to Pad Low	6.4	7.2	8.2	9.8	14.2	ns
t _{ENZH}	Enable Pad Z to High	6.0	6.9	7.9	9.2	13.4	ns
t _{ENZL}	Enable Pad Z to Low	8.3	9.4	10.7	12.7	18.5	ns
t _{ENHZ}	Enable Pad High to Z	10.0	11.6	13.1	15.4	22.4	ns
t _{ENLZ}	Enable Pad Low to Z	9.0	10.4	11.8	13.9	20.2	ns
d _{TLH}	Delta Low to High	0.10	0.11	0.13	0.15	0.22	ns/pF
d _{THL}	Delta High to Low	0.06	0.07	0.08	0.09	0.13	ns/pF

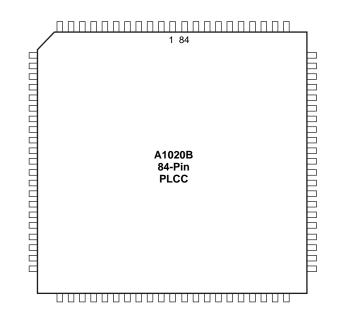
(Worst-Case Commercial Conditions)

Notes:

1. Delays based on 35 pF loading.

2. SSO information can be found in the "Simultaneous Switching Output Limits for Actel FPGAs" application note on page 4-125.

84-Pin PLCC



Signal	A1020B, A10V20B Function	
4	VCC	
12	NC	
18	GND	
19	GND	
25	VCC	
26	VCC	
33	VCC	
40	GND	
46	VCC	
60	GND	
61	GND	
64	CLK, I/O	
66	MODE	
67	VCC	
68	VCC	
72	SDI, I/O	
73	DCLK, I/O	
74	PRA, I/O	
75	PRB, I/O	
82	GND	

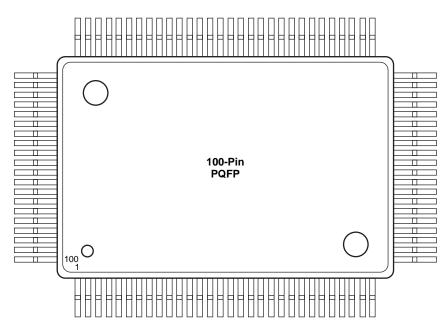
Notes:

1. NC: Denotes No Connection

2. All unlisted pin numbers are user I/Os.



100-Pin PQFP



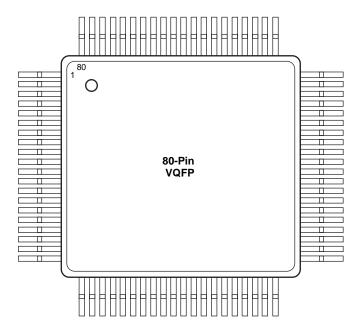
Pin	A1010B Function	A1020B Function	Pin	A1010B Function	A1020B Function
1	NC	NC	53	NC	NC
2	NC	NC	54	NC	NC
3	NC	NC	55	NC	NC
4	NC	NC	56	VCC	VCC
5	NC	NC	63	GND	GND
6	PRB, I/O	PRB, I/O	69	VCC	VCC
13	GND	GND	77	NC	NC
19	VCC	VCC	78	NC	NC
27	NC	NC	79	NC	NC
28	NC	NC	80	NC	I/O
29	NC	NC	81	NC	I/O
30	NC	NC	82	NC	I/O
31	NC	I/O	86	GND	GND
32	NC	I/O	87	GND	GND
33	NC	I/O	90	CLK, I/O	CLK, I/O
36	GND	GND	92	MODE	MODE
37	GND	GND	93	VCC	VCC
43	VCC	VCC	94	VCC	VCC
44	VCC	VCC	95	NC	I/O
48	NC	I/O	96	NC	I/O
49	NC	I/O	97	NC	I/O
50	NC	I/O	98	SDI, I/O	SDI, I/O
51	NC	NC	99	DCLK, I/O	DCLK, I/O
52	NC	NC	100	PRA, I/O	PRA, I/O

Notes:

1. NC: Denotes No Connection

2. All unlisted pin numbers are user I/Os.

80-Pin VQFP



Pin	A1010B, A10V10B Function	A1020B, A10V20B Function		Pin	A1010B, A10V10B Function	A1020B, A10V20B Function
2	NC	I/O	1	47	GND	GND
3	NC	I/O		50	CLK, I/O	CLK, I/O
4	NC	I/O		52	MODE	MODE
7	GND	GND		53	VCC	VCC
13	VCC	VCC		54	NC	I/O
17	NC	I/O		55	NC	I/O
18	NC	I/O		56	NC	I/O
19	NC	I/O		57	SDI, I/O	SDI, I/O
20	VCC	VCC		58	DCLK, I/O	DCLK, I/O
27	GND	GND		59	PRA, I/O	PRA, I/O
33	VCC	VCC		60	NC	NC
41	NC	I/O		61	PRB, I/O	PRB, I/O
42	NC	I/O		68	GND	GND
43	NC	I/O		74	VCC	VCC

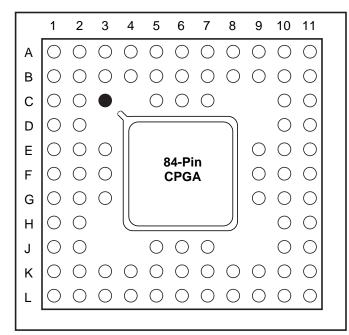
Notes:

1. NC: Denotes No Connection

2. All unlisted pin numbers are user I/Os.



84-Pin CPGA



Orientation Pin (C3)

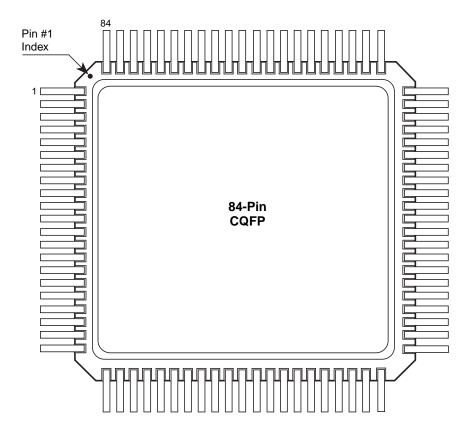
Pin	A1010B Function	A1020B Function	Pin	A1010B Function	A1020B Function
A11	PRA, I/O	PRA, I/O	E10	VCC	VCC
B1	NC	I/O	E11	MODE	MODE
B2	NC	NC	F1	VCC	VCC
B5	VCC	VCC	F9	CLK, I/O	CLK, I/O
B7	GND	GND	F10	GND	GND
B10	PRB, I/O	PRB, I/O	G2	VCC	VCC
B11	SDI, I/O	SDI,I/O	G10	GND	GND
C1	NC	I/O	J2	NC	I/O
C2	NC	I/O	J10	NC	I/O
C10	DCLK, I/O	DCLK, I/O	K1	NC	I/O
C11	NC	I/O	K2	VCC	VCC
D10	NC	I/O	K5	GND	GND
D11	NC	I/O	K7	VCC	VCC
E2	GND	GND	K10	NC	I/O
E3	GND	GND	K11	NC	I/O
E9	VCC	VCC	L1	NC	I/O

Notes:

1. NC: Denotes No Connection

2. All unlisted pin numbers are user I/Os.

84-Pin CQFP



Pin	A1020B Function	Pin	A1020B Function	
1	NC	53	CLK, I/O	_
7	GND	55	MODE	
8	GND	56	VCC	
14	VCC	57	VCC	
15	VCC	61	SDI, I/O	
22	VCC	62	DCLK, I/O	
29	GND	63	PRA, I/O	
35	VCC	64	PRB, I/O	
49	GND	71	GND	
50	GND	77	VCC	

Notes:

1. NC: Denotes No Connection

2. All unlisted pin numbers are user I/Os.

